

Listing of the Claims

Claims 1- 23(canceled)

Claim 24. (currently amended): A method comprising:

exposing a semiconductor wafer to a first mask part that is at least partially defective; and,

exposing the semiconductor wafer to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations, said first mask part and said second ~~mask~~ mask part are on different photomasks.

Claim 25. (previously presented): The method of claim 24, further comprising exposing the semiconductor wafer to the second mask part a second time.

Claim 26. (previously presented): The method of claim 25, further comprising exposing the semiconductor wafer to the second mask part a third time.

Claim 27. (previously presented): The method of claim 24, further comprising exposing the semiconductor wafer to the

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second mask part one or more additional times.

Claim 28. (previously presented): The method of claim 24 further comprising exposing the semiconductor wafer to the second, a third and other additional mask parts one or more additional times.

Claim 29. (previously presented): The method of claim 24, wherein the first mask part comprises a layout for a semiconductor device that is at least partially defective, and the second mask part comprises a layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

Claim 30. (previously presented): The method of claim 24, wherein exposing the semiconductor wafer to the first mask part and exposing the semiconductor wafer to the second mask part are part of a lithographic semiconductor fabrication process.

Claim 31. (previously presented): A method comprising:

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exposing a semiconductor wafer to a first mask part comprises a layout for a semiconductor device that is at least partially defective; and

exposing the semiconductor wafer to a second mask part corresponding to the first mask part comprises a layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

Claim 32. (previously presented): The method of claim 31, wherein the first mask part and the second mask part are on a same photomask.

Claim 33. (previously presented): The method of claim 31, wherein the first mask part and the second mask part are on different photomasks.

Claim 34. (previously presented): The method of claim 31, further comprising exposing the semiconductor wafer to the second mask part a second time.

Claim 35. (previously presented): The method of claim 31,

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further comprising exposing the semiconductor wafer to the second mask part a third time.

Claim 36. (previously presented): The method of claim 31, further comprising exposing the semiconductor wafer to the second mask part one or more additional times.

Claim 37. (previously presented): The method of claim 31 further comprising exposing the semiconductor wafer to the second, a third and other additional mask parts one or more additional times.

Claim 38. (previously presented): The method of claim 31, wherein exposing the semiconductor wafer to the first mask part and exposing the semiconductor wafer to the second mask part are part of a lithographic semiconductor fabrication process.